

**Type 2N3700UB**

**Geometry 4500**

**Polarity NPN**

**Qual Level: JAN - JANS**

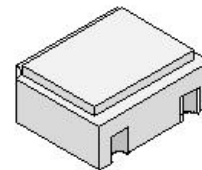
**Generic Part Number:  
2N3700UB**

**REF: MIL-PRF-19500/391**

**Features:**

[Request Quotation](#)

- General-purpose low power silicon transistor.
- Housed in a [cersot](#) case.
- Also available in chip form using the [4500](#) chip geometry.
- The Min and Max limits shown are per [MIL-PRF-19500/391](#) which Semicoa meets in all cases.
- [Radiation graphs available.](#)



Cersot

**Maximum Ratings**

$T_C = 25^{\circ}\text{C}$  unless otherwise specified

Rating	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	V
Collector-Base Voltage	$V_{CBO}$	140	V
Emitter-Base Voltage	$V_{EBO}$	7.0	V
Collector Current, Continuous	$I_C$	1.0	A
Operating Junction Temperature	$T_J$	-55 to +200	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55 to +200	$^{\circ}\text{C}$

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise specified

OFF Characteristics	Symbol	Min	Max	Unit
Collector-Base Breakdown Voltage $I_C = 100 \mu\text{A}$	$V_{(BR)CBO}$	140	---	V
Collector-Emitter Breakdown Voltage $I_C = 30 \text{ mA}$	$V_{(BR)CEO}$	80	---	V
Emitter-Base Breakdown Voltage $I_E = 100 \mu\text{A}$	$V_{(BR)EBO}$	7.0	---	V
Collector-Emitter Cutoff Current $V_{CE} = 90 \text{ V}$	$I_{CES}$	---	10	nA
Emitter-Base Cutoff Current $V_{EB} = 5 \text{ V}$	$I_{EBO}$	---	10	nA

ON Characteristics	Symbol	Min	Max	Unit
<b>DC Current Gain</b>				
$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}$	$h_{FE1}$	100	300	---
$I_C = 0.1 \text{ mA}, V_{CE} = 10 \text{ V}$	$h_{FE2}$	50	200	---
$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ (pulsed)	$h_{FE3}$	90	---	---
$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}$ (pulsed)	$h_{FE4}$	50	200	---
$I_C = 1 \text{ A}, V_{CE} = 10 \text{ V}$ (pulsed)	$h_{FE5}$	15	---	---
<b>Base-Emitter Saturation Voltage</b>				
$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ (pulsed)	$V_{BE(sat)}$	---	1.1	V dc
<b>Collector-Emitter Saturation Voltage</b>				
$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ (pulsed)	$V_{CE(sat)1}$	---	0.2	V dc
$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$ (pulsed)	$V_{CE(sat)2}$	---	0.5	V dc

Small Signal Characteristics	Symbol	Min	Max	Unit
<b>Short Circuit Forward Current Transfer Ratio</b> $I_C = 1 \text{ mA}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$	AC $h_{FE}$	80	400	---
<b>Magnitude of Common Emitter, Small Signal, Short Circuit Forward Current Transfer Ratio</b> $V_{CE} = 10 \text{ V}, I_C = 50 \text{ mA}, f = 200 \text{ MHz}$	$ h_{FE} $	5.0	20	---
<b>Open Circuit Output Capacitance</b> $V_{CB} = 10 \text{ V}, I_E = 0, 100 \text{ kHz} < f < 1 \text{ MHz}$	$C_{OBO}$	---	12	pF
<b>Input Capacitance, Output Open Circuited</b> $V_{EB} = 2.0 \text{ V}, I_C = 0, 100 \text{ kHz} < f < 1 \text{ MHz}$	$C_{IBO}$	---	60	pF
<b>Collector-Base Time Constant</b> $V_{CB} = 10 \text{ V}, I_C = 10 \text{ mA}, f = 79.8 \text{ MHz}$	$r_b' C_C$	---	400	ps
<b>Noise Figure</b> $V_{CE} = 10 \text{ V}, I_C = 100 \mu\text{A}, R_g = 1 \text{ k}\Omega$	NF	---	4	dB

Switching Characteristics	Symbol	Min	Max	Unit
<b>Pulse Response</b> 15 ns, 50 ohm input pulse	$t_{ON} + t_{OFF}$	---	30	ns